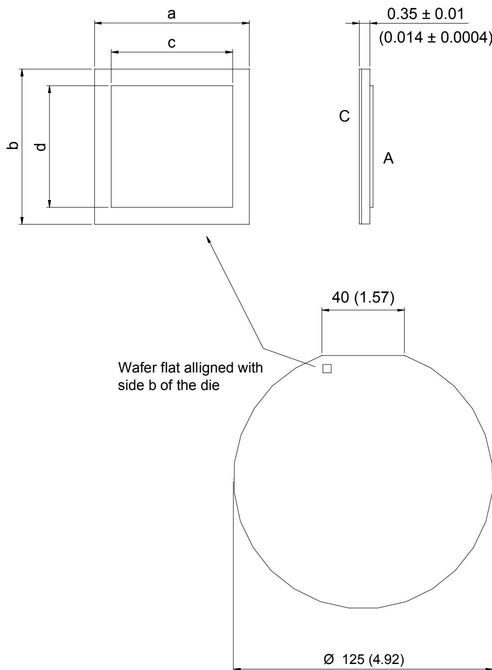
FD087U02A5B

Fred Die in Wafer Form



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
2. CONTROLLING DIMENSION (INCH):
3. DIMENSIONS AND TOLERANCES:
   a = 2.210 ± 0.05
   (0.087 ± 0.002)
   b = 2.210 ± 0.05
   (0.087 ± 0.002)
   c = 1.996 ± 0.003
   (0.078 ± 0.0001)
   d = 1.996 ± 0.003
   (0.078 ± 0.0001)
4. LETTER DESIGNATION:
   A = Anode (Top Metal)
   C = Cathode (Back Metal)
5. SAWING:
   Recommended Blade
   SEMITEC S1025 QS00 Blade
6. MINIMUM ORDER QUANTITY:
   1300 die

NOT TO SCALE

Reference IR Packaged Part: MUR820 Series

Electrical Characteristics (Wafer Form)

	Parameters	Units	Test Conditions
V_{FM}	Maximum Forward Voltage	0.975 V	T_J = 25°C, I_F = 8 A
V_{RRM}	Mimunum Reverse Breakdown Voltage	200 V	T_J = 25°C, I_{RRM} = 100 µA
I_{RM}	Max. Reverse Leakage Current	5µA	T_J = 25°C, V_{RRM} = 200 V
t_{rr}	Typ. Reverse Recovery Time	35ns	I_F = 1A, di_F/ dt = 50A/µs, V_R = 30 V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 2 KA - 3 KA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.087" x 0.087" (see drawing)
Reject Ink Dot Size	0.25 mm diameter minimum
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

FD	087	U	02	A	5	B
1	2	3	4	5	6	7

1 - Fred Die
2 - Chip Dimension in Mils: 087 = 087x087 square
3 - Process U = UltraFast
4 - Voltage code Vrrm (*100) eg: 02 = 200V
5 - Chip surface metallization: A = Aluminium (anode), Silver (cathode)
6 - Wafer diameter in inches
7 - Packaging: B = Inked Probed Unsawn Wafer (Wafer in box)